Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	3.5	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

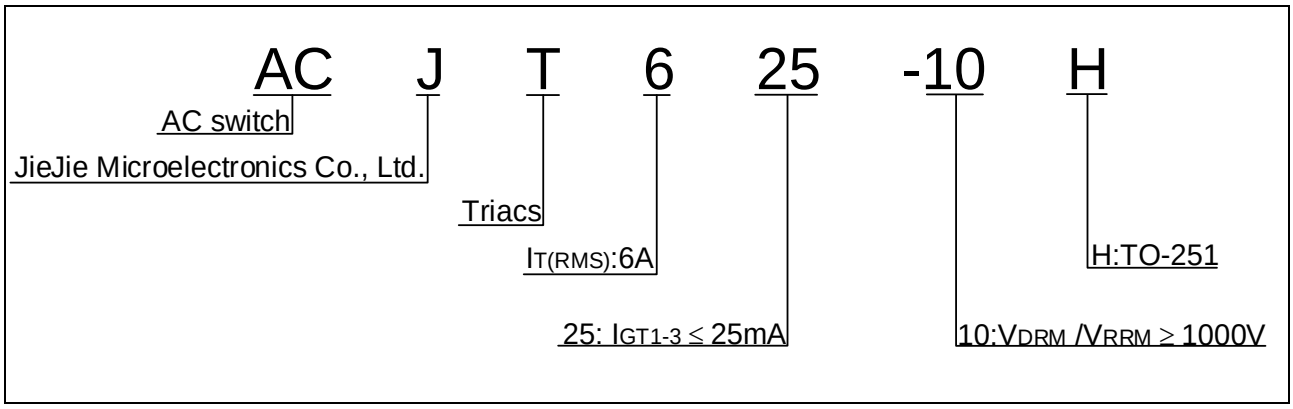
Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	25	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =125 R_L =3.3kΩ	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	40	mA
				60	
I_H	I_T =100mA		MAX.	40	mA
dV/dt	V_D=670V Gate Open T_j =125		MIN.	1500	V/μs
(dI/dt)c	(dV/dt)c=20V/μs, T_j=125		MIN.	8	A/ms
t_{on}	I_G=40mA I_A=200mA I_R=20mA T_j=25		TYP.	5	μs
t_{off}				70	
V_{CL}	I_{CL}=0.1mA t_p=1ms		MIN.	1050	V

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM} =8.5A t_p=380μs	T_j=25	1.5	V
V_{TO}	Threshold voltage	T_j=125	0.82	V
R_D	Dynamic resistance	T_j=125	64	mΩ
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25	8	μA
I_{RRM}		T_j=125	0.5	mA

THERMAL T s b i T @ H

ORDERING INFORMATION



MARKING

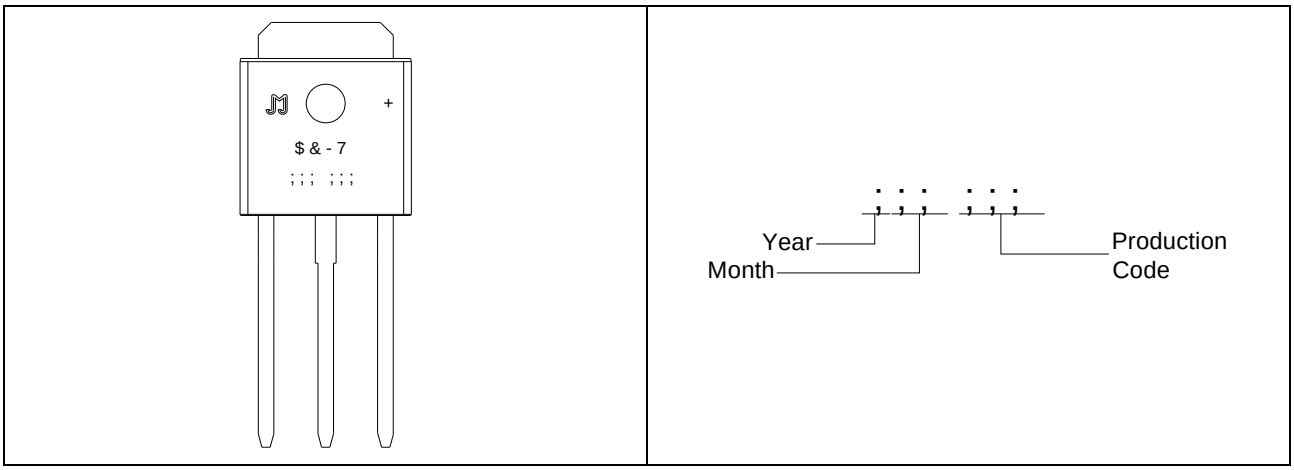


FIG.1: Maximum power dissipation versus RMS on-state current

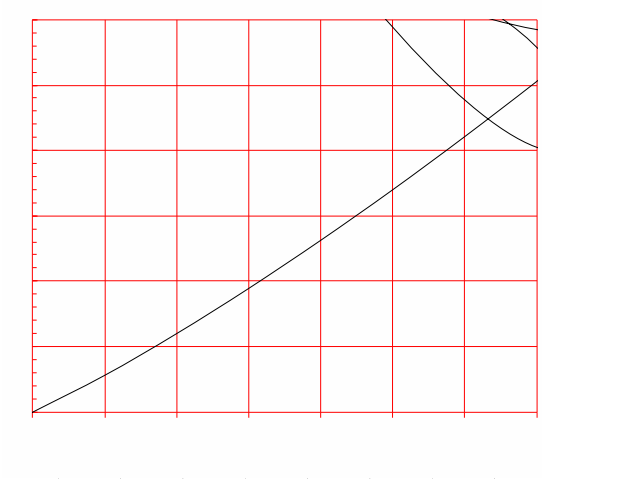
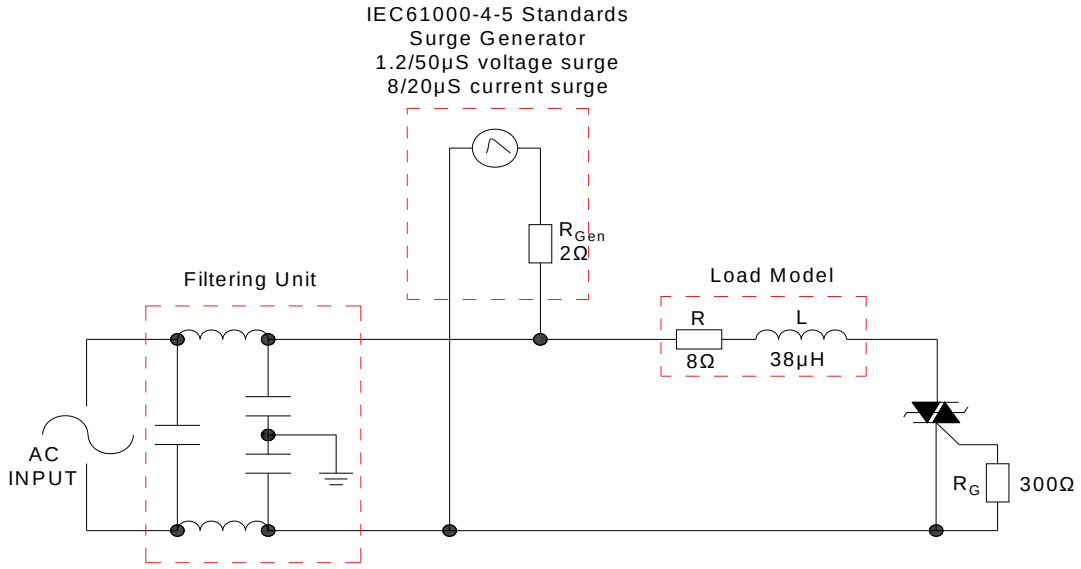


FIG.2: RMS on-state current versus case temperature

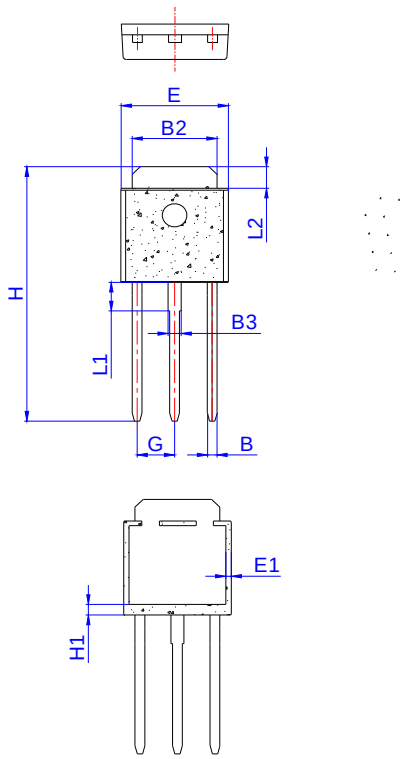
FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	1.00		1.30	0.039		0.051
B	0.50		0.70	0.020		0.028
B2	5.10		5.40	0.200		0.213
B3						
C						
C2						
D						
E						
E1	0.60		1.00	0.024		0.039
G						
H	16.00		17.00	0.630		0.669
H1	1.45		1.85	0.057		0.073
L1						

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